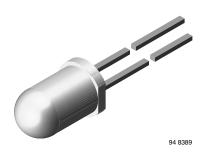
TSHF6410



Vishay Semiconductors

High Speed Infrared Emitting Diode, 890 nm, GaAlAs Double Hetero



DESCRIPTION

TSHF6410 is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- · Package type: leaded
- Package form: T-1³/₄
- Dimensions (in mm): \varnothing 5
- Peak wavelength: $\lambda_p = 890 \text{ nm}$
- · High reliability
- · High radiant power
- · High radiant intensity
- Angle of half intensity: $\varphi = \pm 22^{\circ}$
- · Low forward voltage
- · Suitable for high pulse current operation
- High modulation bandwidth: $f_c = 12 \text{ MHz}$
- · Good spectral matching with Si photodetectors
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

Note

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK coded, 450 kHz or 1.3 MHz)

PRODUCT SUMMARY				
COMPONENT	l _e (mW/sr)	φ (deg)	λ _P (nm)	tr (ns)
TSHF6410	70	± 22	890	30

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSHF6410	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾	

Note

• MOQ: minimum order quantity

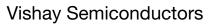
ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	5	V
Forward current		I _F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA
Surge forward current	t _p = 100 μs	I _{FSM}	1.5	А
Power dissipation		Pv	160	mW
Junction temperature		Tj	100	°C
Operating temperature range		T _{amb}	- 40 to + 85	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	$t \leq 5$ s, 2 mm from case	T _{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R _{thJA}	230	K/W

Rev. 1.3, 23-Aug-11

1 For technical questions, contact: <u>emittertechsupport@vishav.com</u> Document Number: 81832



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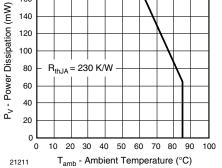


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

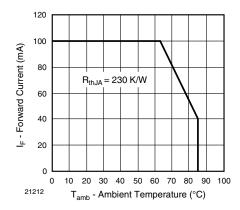


Fig. 1 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	l _F = 100 mA, t _p = 20 ms	V _F		1.4	1.6	V
	I _F = 1 A, t _p = 100 μs	V _F		2.3		V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μA
Junction capacitance	$V_{R} = 0 V, f = 1 MHz, E = 0$	Cj		125		pF
D F 1 1 1	l _F = 100 mA, t _p = 20 ms	l _e	45	70	135	mW/sr
Radiant intensity	I _F = 1 A, t _p = 100 μs	l _e		700		mW/sr
Radiant power	l _F = 100 mA, t _p = 20 ms	φ _e		50		mW
Temperature coefficient of ϕ_{e}	I _F = 100 mA	TKφe		- 0.35		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	I _F = 100 mA	λ _p		890		nm
Spectral bandwidth	I _F = 100 mA	Δλ		40		nm
Temperature coefficient of λ_p	I _F = 100 mA	ΤΚλρ		0.25		nm/K
Rise time	I _F = 100 mA	t _r		30		ns
Fall time	I _F = 100 mA	t _f		30		ns
Cut-off frequency	$I_{DC} = 70$ mA, $I_{AC} = 30$ mA pp	f _c		12		MHz
Virtual source diameter		d		2.1		mm



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BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

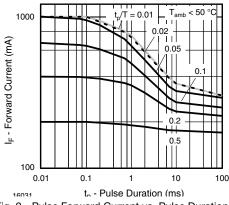


Fig. 2 - Pulse Forward Current vs. Pulse Duration

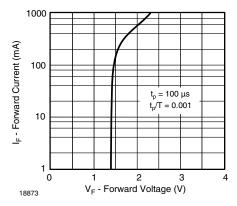


Fig. 3 - Forward Current vs. Forward Voltage

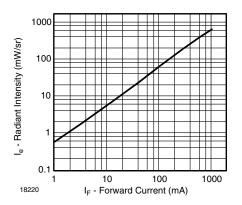


Fig. 4 - Radiant Intensity vs. Forward Current

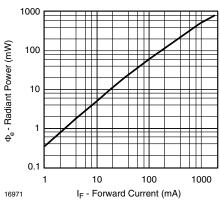


Fig. 5 - Radiant Power vs. Forward Current

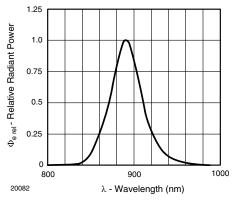


Fig. 6 - Relative Radiant Power vs. Wavelength

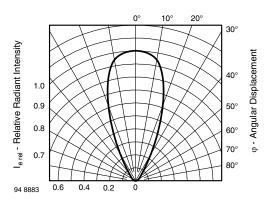


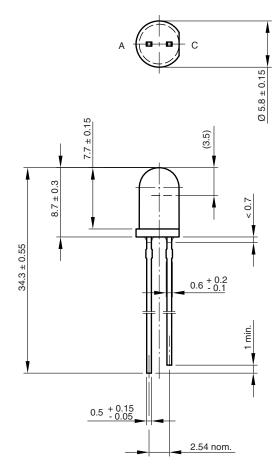
Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

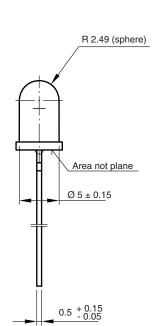
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PACKAGE DIMENSIONS in millimeters







technical drawings according to DIN specifications

Drawing-No.: 6.544-5259.06-4 Issue: 6; 19.05.09 19257



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